

**METHOD FOR MANUFACTURING DEVICE SUBSTRATE
WITH METAL BACK-GATE AND STRUCTURE FORMED THEREBY**

ABSTRACT OF THE DISCLOSURE

A method (and resultant structure) of forming a semiconductor device, includes

5 forming a metal-back-gate over a substrate and a metal back-gate, forming a passivation layer on the metal back-gate to prevent the metal back-gate from reacting with radical species, and providing an intermediate gluing layer between the substrate and the metal back-gate to enhance adhesion.

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